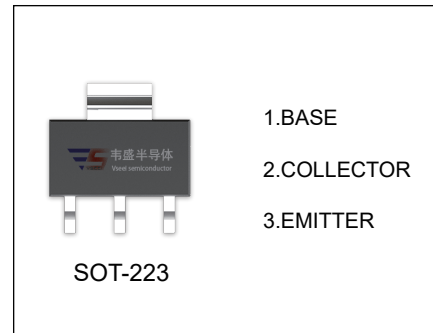


## PZTA42 TRANSISTOR (NPN)

### FEATURES

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: PZTA92(PNP)



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	300	V
V <sub>CEO</sub>	Collector-Emitter Voltage	300	V
V <sub>EB0</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	0.2	A
I <sub>CM</sub>	Collector Current -Pulsed	0.5	A
P <sub>C</sub>	Collector Power Dissipation	1	W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~150	°C

### MARKING:



### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	300			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	300			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =200V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =6V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	25			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	40			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =30mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			0.9	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz	50			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0, f=1MHz			3	pF

